## **SQ2325ES**

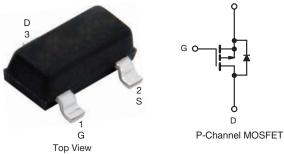


**Vishay Siliconix** 

## Automotive P-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-150			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	1.77			
I <sub>D</sub> (A)	-0.84			
Configuration	Single			

#### SOT-23 (TO-236)



#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 %  $R_{\rm q}$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>



COMPLIANT HALOGEN

Marking	Code:	8Rxxx
maining	oouc.	

ORDERING INFORMATION			
Package	SOT-23		
Lead (Pb)-free and Halogen-free	SQ2325ES-T1-GE3		

<b>ABSOLUTE MAXIMUMRATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	-150	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current	T <sub>C</sub> = 25 °C	Ι <sub>D</sub>	-0.84		
Continuous Drain Current	T <sub>C</sub> = 125 °C		-0.48		
Continuous Source Current (Diode Conduction	on)	I <sub>S</sub>	-3.7	А	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	-2		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	4.8		
Single Pulse Avalanche Energy		E <sub>AS</sub>	1.12	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	3	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1	vv	
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	166	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	50	0/10	

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. When mounted on 1" square PCB (FR4 material).

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**SQ2325ES** 

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = -250 μA	-150	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-2.5	-3	-3.5	v	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{V}_{\text{GS}} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = -150 V	-	-	-1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = -150 V, T <sub>J</sub> = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	$V_{DS}$ = -150 V, $T_{J}$ = 175 °C	-	-	-150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = -10 \text{ V}$	$V_{DS} \ge 5 V$	-0.8	-	-	Α	
		$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -0.5 A	-	1.3	1.77		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -0.5 A, T <sub>J</sub> = 125 °C	-	-	3.4	Ω	
		$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -0.5 A, T <sub>J</sub> = 175 °C	-	-	4.4		
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -0.5 A		-	2.2	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	200	250		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -50 V, f = 1 MHz	-	20	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	17	22		
Total Gate Charge <sup>c</sup>	Qg			-	7.4	10		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = -10 \text{ V}$	$V_{DS} = -75 \text{ V}, \text{ I}_{D} = -0.5 \text{ A}$	-	1.1	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.9	-	1	
Gate Resistance	Rg	f = 1 MHz		2.8	3.9	6.1	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD}$ = -75 V, R <sub>L</sub> = 150 $\Omega$ I <sub>D</sub> $\cong$ -0.5 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 $\Omega$		-	8	12		
Rise Time <sup>c</sup>	t <sub>r</sub>			-	14	18	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	15	20		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	10	14	1	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-2	Α	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

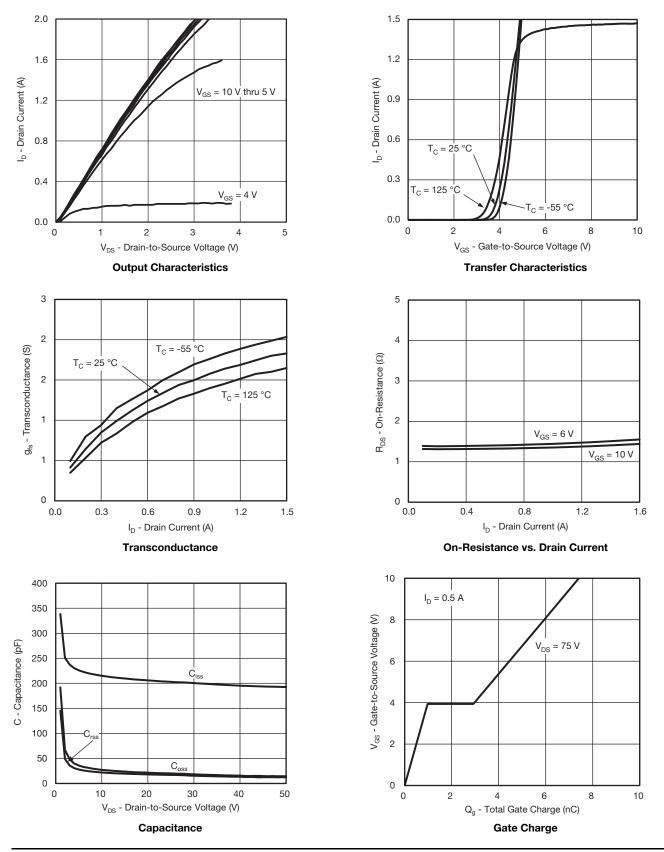


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#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S15-0188-Rev. B, 16-Feb-15

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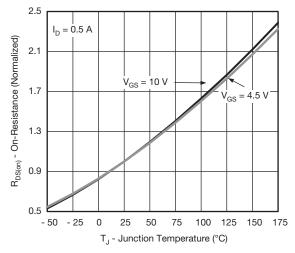
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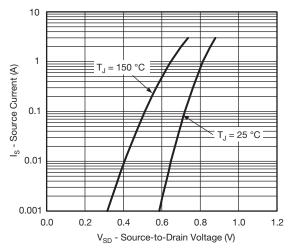
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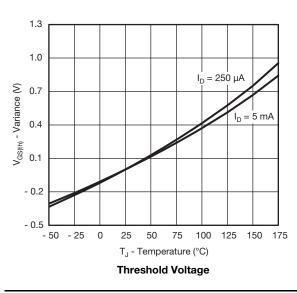
#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



**On-Resistance vs. Junction Temperature** 



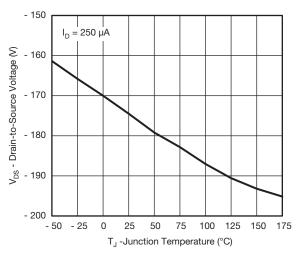
Source-Drain Diode Forward Voltage



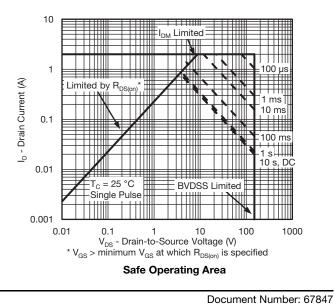
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5.0 4.0  $R_{DS(on)}$  - On-Resistance ( $\Omega$ ) 3.0 2.0 T<sub>J</sub> = 150 °C 1.0 T<sub>J</sub> = 25 °C 0.0 2 0 4 6 8 10 V<sub>GS</sub> - Gate-to-Source Voltage (V)

**On-Resistance vs. Gate-to-Source Voltage** 



Drain Source Breakdown vs. Junction Temperature



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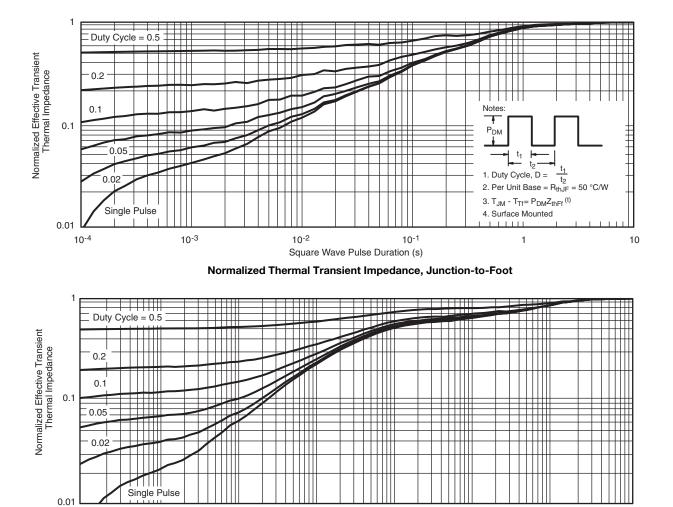
4





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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

10-1



1

10

100

1000

#### Note

10-4

• The characteristics shown in the two graphs

10<sup>-3</sup>

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

10-2

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg267847">www.vishay.com/ppg267847</a>.

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## **SQ2325ES**

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#### **REVISION HISTORY**<sup>a</sup>

REVISION	DATE	DESCRIPTION OF CHANGE		
В	30-Jan-15	Redesigned to meet AEC-Q101 rev D.		

Note

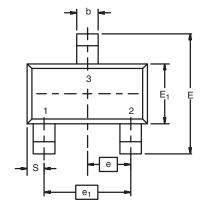
a. As of April 2014



## Package Information

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#### SOT-23 (TO-236): 3-LEAD







Dim	MILLIM	IETERS	INCHES		
Dim	Min	Мах	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01				



# Application Note 826

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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